

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

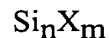
1. (Previously Amended) A method for forming a silicon film, comprising:
applying by patterning an ink composition containing a silicon compound onto a substrate by an ink jet process, the silicon compound having at least one cyclic structure.

2. (Previously Amended) The method for forming a silicon film according to claim 1, the ink composition being applied in an inert atmosphere.

3. (Previously Amended) The method for forming a silicon film according to claim 1, further comprising: a drying step of removing a solvent of the composition; and a step of pyrolyzing and/or photolyzing in the coating film.

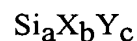
4. (Previously Amended) The method for forming a silicon film according to claim 3, further comprising:
a step for irradiating the silicon film formed by heat treatment and/or light treatment with laser to convert the amorphous silicon film into a polycrystalline silicon film.

5. (Currently Amended) The method for forming a silicon film according to claim 1, the silicon compound is a silicon compound represented by



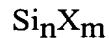
n representing an integer of 3 or more, m representing an integer of n, $2n-2$, or $2n$, ~~or $2n+2$~~ , and X representing a hydrogen atom and/or a halogen atom.

6. (Currently Amended) The method for forming a silicon film according to claim 1, the silicon compound is a silicon compound represented by



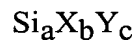
X representing a hydrogen atom ~~and/or a halogen atom~~, Y representing a boron atom or a phosphorus atom, a representing an integer of 3 or more, b representing an integer of a to $2a+c$ ~~$2a+c+2$~~ , and c representing an integer of 1 to a.

7. (Currently Amended) The method for forming a silicon film according to claim 1, the silicon compound is a composition containing a silicon compound represented by the following general formula and a silicon compound represented by



n representing an integer of 3 or more, m representing an integer of n, $2n-2$, or $2n$, ~~or $2n+2$~~ , and X representing a hydrogen atom and/or a halogen atom; and

silicon compound represented by



X representing a hydrogen atom ~~and/or a halogen atom~~, Y representing a boron atom or a phosphorus atom, a representing an integer of 3 or more, b representing an integer of a to $2a+c$ ~~$2a+c+2$~~ , and c representing an integer of 1 to a, at least one of the compounds satisfying one of the formulae is cyclic.

8. (Previously Amended) The method for forming a silicon film according to claim 5, n being in a range of 5 to 20.

9. (Previously Amended) The method for forming a silicon film according to claim 6, a+c being in a range of 5 to 20.

10. (Previously Amended) The method for forming a silicon film according to claim 1, the silicon compound being dissolved in at least one solvent having a vapor pressure at room temperature of 0.001 to 50 mmHg.

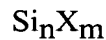
11. (Previously Amended) The method for forming a silicon film according to claim 10, the solvent being a hydrocarbon solvent.

12. (Previously Amended) The method for forming a silicon film according to claim 1, the concentration of the silicon compound in the composition being in a range of 0.01 to 10 percent by weight.

13. (Currently Amended) The method for forming a silicon film according to claim 1, the composition ~~being having~~ a viscosity of 1 to 50 mPa·s and a surface tension of 20 to 70 dyn/cm.

14. (Currently Amended) An ink-jet ink composition for forming a silicon film, comprising:

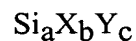
a silicon compound represented



n representing an integer of 3 or more, m representing an integer of n, $2n-2$, or $2n$, ~~or $2n+2$,~~ and X representing a hydrogen atom and/or a halogen atom, the silicon compound having at least one cyclic structure.

15. (Currently Amended) An ink-jet ink composition for forming a silicon film, comprising:

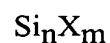
a silicon compound represented by



X representing a hydrogen atom ~~and/or a halogen atom~~, Y representing a boron atom or a phosphorus atom, a representing an integer of 3 or more, b representing an integer of a to $2a+c$ ~~$2a+c+2$~~ , and c representing an integer of 1 to a, the silicon compound having at least one cyclic structure.

16. (Currently Amended) An ink-jet ink composition for forming a silicon film, comprising:

a silicon compound represented by



n representing an integer of 3 or more, m representing an integer of n, $2n-2$, or $2n$, ~~or $2n+2$~~ ,
and X representing a hydrogen atom and/or a halogen atom; and

a silicon compound represented by



X representing a hydrogen atom ~~and/or a halogen atom~~, Y representing a boron atom or a phosphorus atom, a representing an integer of 3 or more, b representing an integer of a to ~~$2a+c$~~ $2a+c+2$, and c representing an integer of 1 to a.

17. (Previously Amended) The ink composition according to claim 14, n being in a range of 5 to 20.

18. (Previously Amended) The ink composition according to claim 15, wherein a+c being in a range of 5 to 20.

19. (Previously Amended) The ink composition according to claim 14, the silicon compound being dissolved in at least one solvent having a vapor pressure at room temperature of 0.001 to 50 mmHg.

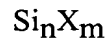
20. (Previously Amended) The ink composition according to claim 19, the solvent being a hydrocarbon solvent.

21. (Previously Amended) The ink composition according to claim 14, the concentration of the silicon compound in the composition being in a range of 0.01 to 10 percent by weight.

22. (Previously Amended) The ink composition according to claim 14, the composition having a viscosity of 1 to 50 mPa·s and a surface tension of 20 to 70 dyn/cm.

23. (Currently Amended) A method for forming a silicon film, comprising:
applying by patterning an ink composition containing a silicon compound onto a substrate by an ink jet process, the silicon compound is a composition containing a silicon

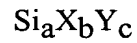
compound represented by the following general formula and a silicon compound represented by



n representing an integer of 3 or more, m representing an integer of n, 2n-2, 2n, or 2n+2, and

X representing a hydrogen atom and/or a halogen atom; and

silicon compound represented by



X representing a hydrogen atom ~~and/or a halogen atom~~, Y representing a boron atom or a

phosphorus atom, a representing an integer of 3 or more, b representing an integer of a to

2a+c+2, and c representing an integer of 1 to a.